

isc Silicon PNP Power Transistor

2SB763

DESCRIPTION

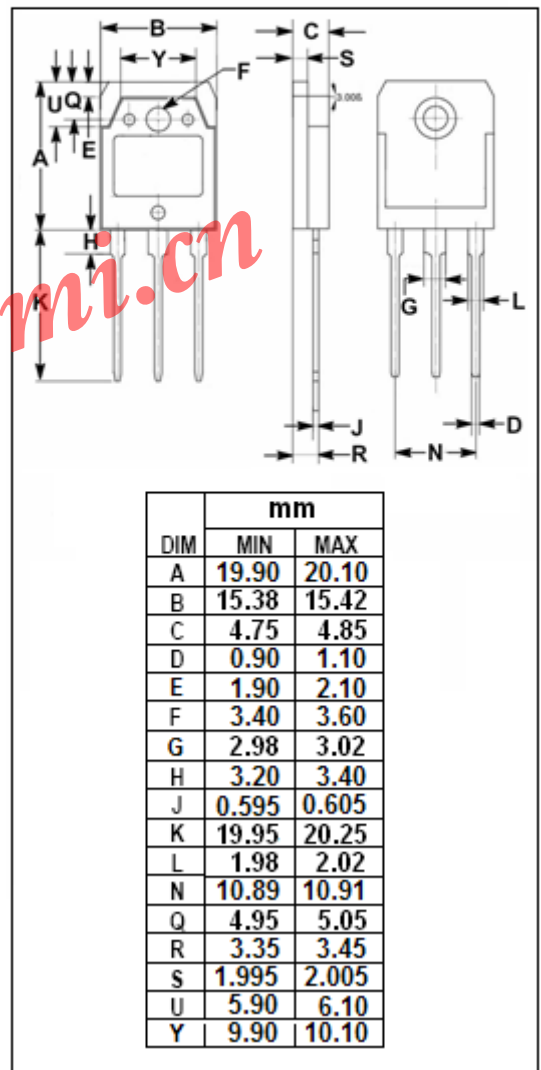
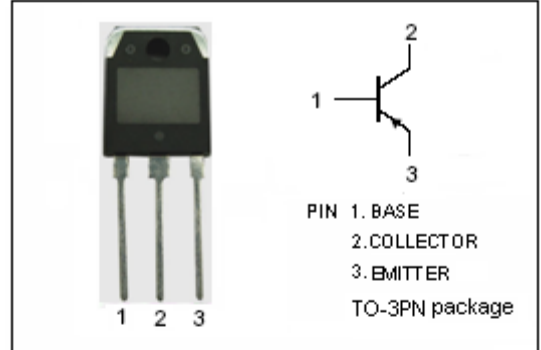
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = -60V(\text{Min})$
- Good Linearity of  $h_{FE}$
- High Collector Power Dissipation
- Complement to Type 2SD858

APPLICATIONS

- Designed for AF power amplifier applications.

ABSOLUTE MAXIMUM RATINGS( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-60	V
$V_{CEO}$	Collector-Emitter Voltage	-60	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current-Continuous	-5	A
$I_{CM}$	Collector Current-Peak	-10	A
$P_C$	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	60	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



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## ELECTRICAL CHARACTERISTICS

 $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -30\text{mA}; I_B = 0$	-60			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -5\text{A}; I_B = -0.5\text{A}$			-1.5	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -3\text{A}; V_{CE} = -4\text{V}$			-1.6	V
$I_{CEO}$	Collector Cutoff Current	$V_{CE} = -30\text{V}; I_B = 0$			-700	$\mu\text{A}$
$I_{CES}$	Collector Cutoff Current	$V_{CE} = -60\text{V}; V_{BE} = 0$			-400	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -5\text{V}; I_C = 0$			-1	mA
$h_{FE-1}$	DC Current Gain	$I_C = -1\text{A}; V_{CE} = -4\text{V}$	40		250	
$h_{FE-2}$	DC Current Gain	$I_C = -3\text{A}; V_{CE} = -4\text{V}$	20			

## Switching Times

$t_{on}$	Turn-On Time	$I_C = -6\text{A}; I_{B1} = -I_{B2} = -0.6\text{A}$		0.2		$\mu\text{s}$
$t_{off}$	Turn-Off Time			1.4		$\mu\text{s}$

◆  $h_{FE-1}$  Classifications

R	Q	P
40-90	70-150	120-250